

30V Dual P-Channel MOSFET



SOP-8

Pin Definition:

1. Source 1 8. Drain 1 2. Gate 1 7. Drain 1 3. Source 2 6. Drain 2 4. Gate 2 5. Drain 2

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)	
-30	60 @ V _{GS} = 10V	-4.9	
	90 @ V _{GS} = 4.5V	-3.7	

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

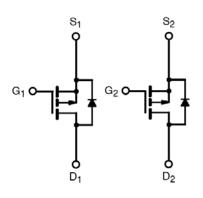
Application

- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing
TSM4953DCS RF	SOP-8	2.5Kpcs / 13" Reel

Block Diagram



Dual P-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	-30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current, V _{GS} @4.5V	' .	I _D	-4.9	Α	
Pulsed Drain Current, V _{GS} @4.5V		I _{DM}	-20	Α	
Continuous Source Current (Diode Co	onduction) ^{a,b}	I _S	-2.6	Α	
Maximum Power Dissipation	Ta = 25°C	D	2.5	W	
	Ta = 70°C	- P _D	1.3		
Operating Junction Temperature		T _J	+150	°C	
Operating Junction and Storage Temp	perature Range	T _J , T _{STG} - 55 to +150		°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	R⊖ _{JC}	40	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RO _{JA}	62.5	°C/W

Notes

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, $t \le 5$ sec.



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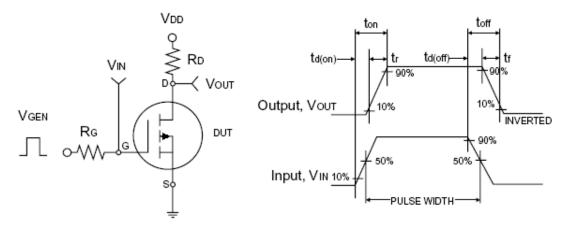
Pb Rohs COMPLIANCE

Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV _{DSS}	-30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-1.0	-1.5	-3.0	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}	I		±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -24V, V_{GS} = 0V$	I _{DSS}	I		-1.0	μA
On-State Drain Current ^a	$V_{DS} = -5V, V_{GS} = -10V$	I _{D(ON)}	-6			Α
Drain-Source On-State Resistance ^a	$V_{GS} = -10V, I_D = -4.9A$			50	60	mΩ
Drain-Source On-State Resistance	$V_{GS} = -4.5V$, $I_{D} = -3.7A$	R _{DS(ON)}	I	75	90	
Forward Transconductance ^a	$V_{DS} = -15V$, $I_{D} = -4.9A$	g _{fs}	I	10		S
Diode Forward Voltage	$I_S = -1.9A$, $V_{GS} = 0V$	V_{SD}	I		-1.3	V
Dynamic ^b						
Total Gate Charge	$V_{DS} = -15V, I_{D} = -4.9A,$	Q_g		28		
Gate-Source Charge	$V_{DS} = -15V, I_D = -4.9A,$ $V_{GS} = -10V$	Q_gs		3		nC
Gate-Drain Charge	V _{GS} = -10V	Q_{gd}	-	7		
Input Capacitance	\\ - 45\\ \\ - 0\\	C _{iss}	I	745		
Output Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		440		pF
Reverse Transfer Capacitance	1 - 1.0IVINZ	C _{rss}	I	120		
Switching ^c						
Turn-On Delay Time	V - 45V D - 450	t _{d(on)}	I	9		
Turn-On Rise Time	$V_{DD} = -15V, R_L = 15\Omega,$ $I_D = -1A, V_{GEN} = -10V,$	t _r	1	15		nS
Turn-Off Delay Time		t _{d(off)}		75		110
Turn-Off Fall Time	$R_G = 6\Omega$	t _f		40		

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

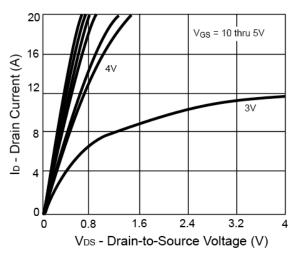


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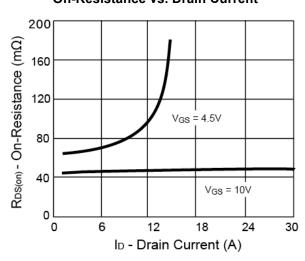


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

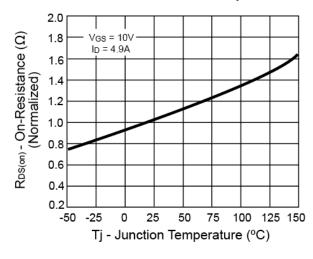




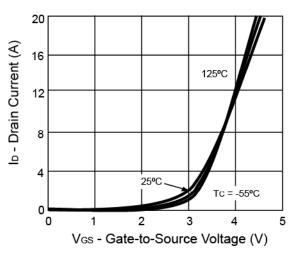
On-Resistance vs. Drain Current



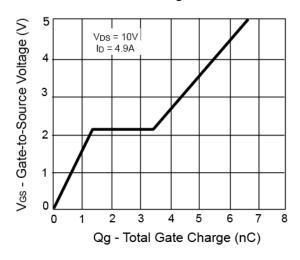
On-Resistance vs. Junction Temperature



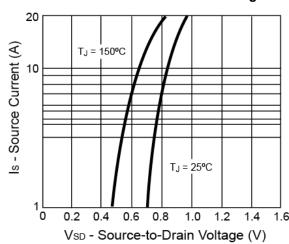
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



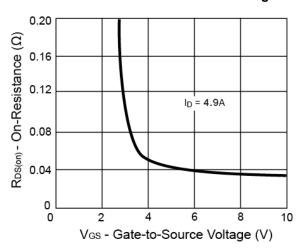


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Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

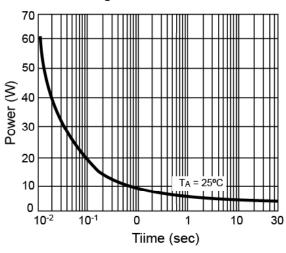
On-Resistance vs. Gate-Source Voltage



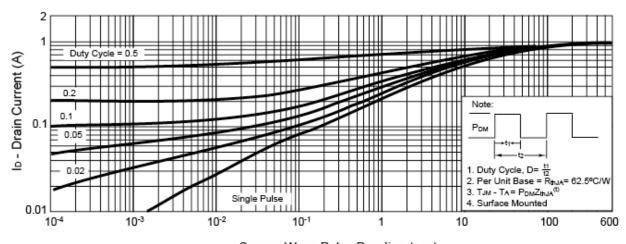
Threshold Voltage 0.8 0.4 0.0 1D = 250µA -0.8 -0.8 -50 -25 0 25 50 75 100 125 150

Tj - Junction Temperature (°C)

Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



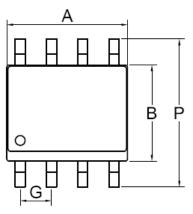
Square Wave Pulse Duration (sec)

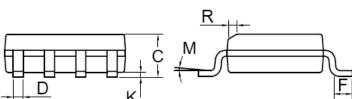


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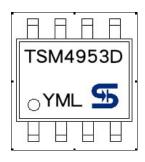
SOP-8 Mechanical Drawing





SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.05	BSC	
K	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

Marking Diagram



Y = Year Code

M = Month Code

(**A**=Jan, **B**=Feb, **C**=Mar, **D**=Apl, **E**=May, **F**=Jun, **G**=Jul, **H**=Aug, **I**=Sep, **J**=Oct, **K**=Nov, **L**=Dec)

L = Lot Code

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Version: B07



TSM4953D 30V Dual P-Channel MOSFET

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